TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

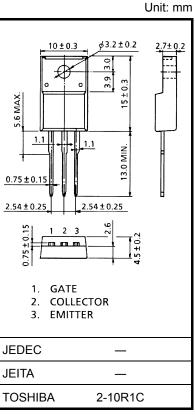
GT15J321

High Power Switching Applications Fast Switching Applications

- Fourth-generation IGBT
- Fast switching (FS
- Enhancement mode type
- High speed: $t_f = 0.03 \,\mu s$ (typ.)
- Low saturation Voltage: VCE (sat) = 1.90 V (typ.)
- FRD included between emitter and collector

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	600	V	
Gate-emitter voltage		V _{GES}	±20	V	
Collector current	DC	Ic	15	Α	
	1 ms	I _{CP}	30		
Emitter-collector forward current	DC	lF	15	Α	
	1 ms	I _{FM}	30		
Collector power dissipation (Tc = 25°C)		PC	30	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

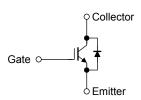


Weight: 1.7 g

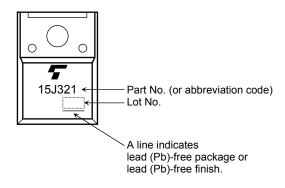
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Equivalent Circuit



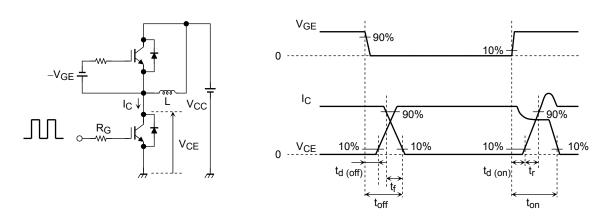
Marking



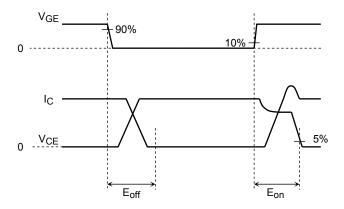
Electrical Characteristics (Ta = 25°C)

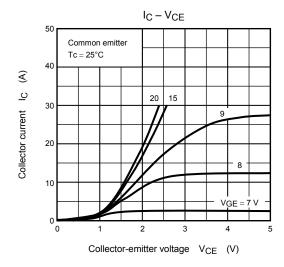
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cur	rent	I _{GES}	$V_{GE} = \pm 20 \text{ V}, V_{CE} = 0$	_	_	±500	nA	
Collector cut-off current		I _{CES}	V _{CE} = 600 V, V _{GE} = 0	_	_	1.0	mA	
Gate-emitter cut-off voltage		V _{GE} (OFF)	I _C = 1.5 mA, V _{CE} = 5 V	3.5	_	6.5	V	
Collector-emitter	saturation voltage	V _{CE} (sat)	I _C = 15 A, V _{GE} = 15 V	_	1.90	2.45	V	
Input capacitance		C _{ies}	$V_{CE} = 20 \text{ V}, V_{GE} = 0, f = 1 \text{ MHz}$	_	2300	_	pF	
Switching time Tur	Rise time	t _r	Inductive Load	_	0.04	_		
	Turn-on time	t _{on}	V _{CC} = 300 V, I _C = 15 A	_	0.17	_	μs	
	Fall time	t _f	V_{GG} = 15 V, R_G = 43 Ω	_	0.03	0.15		
	Turn-off time	t _{off}	(Note 1)	_	0.34	_		
Peak forward voltage		V _F	I _F = 15 A, V _{GE} = 0	_	_	2.0	V	
Reverse recovery time		t _{rr}	I _F = 15 A, di/dt = -100 A/μs	_	_	200	ns	
Thermal resistance (IGBT) Rth (j-c)		R _{th (j-c)}	_	_	_	4.16	°C/W	
Thermal resistance (Diode)		R _{th (j-c)}	_	_	_	4.63	°C/W	

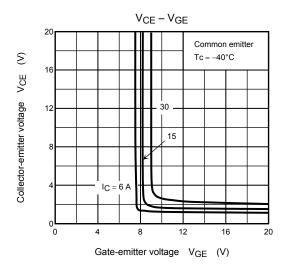
Note 1: Switching time measurement circuit and input/output waveforms

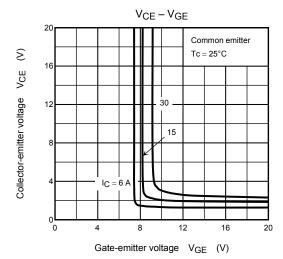


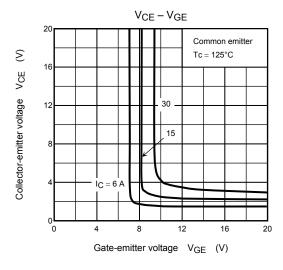
Note 2: Switching loss measurement waveforms

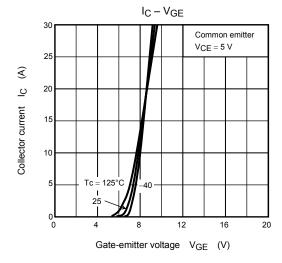


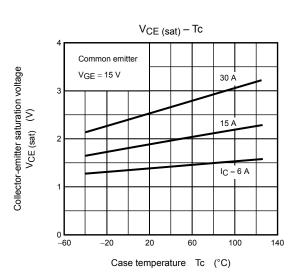




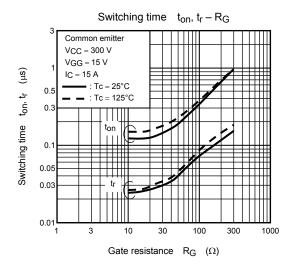


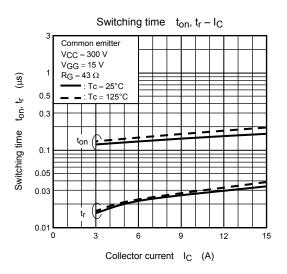


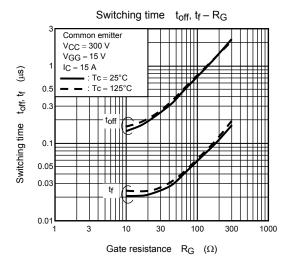


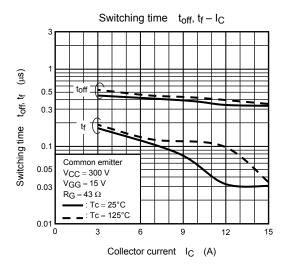


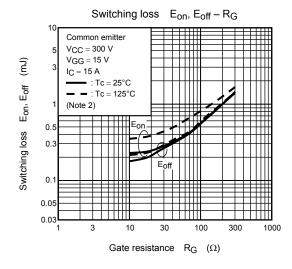
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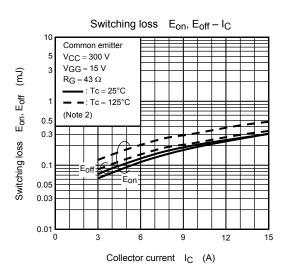


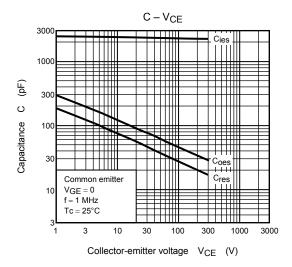


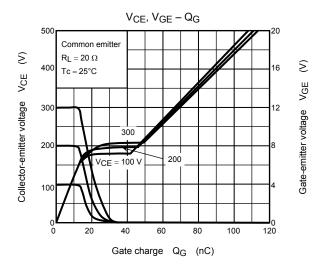


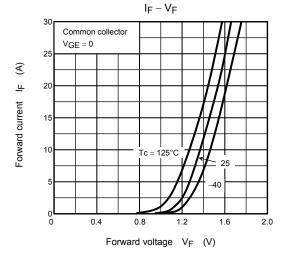


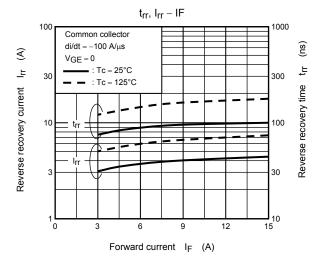


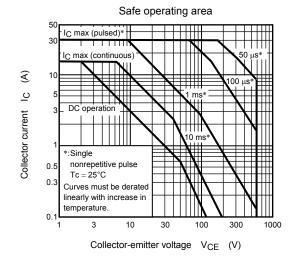


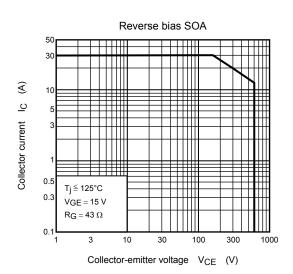




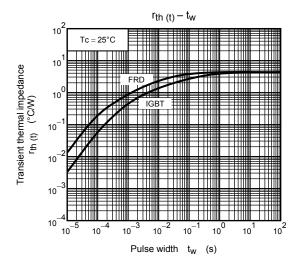








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